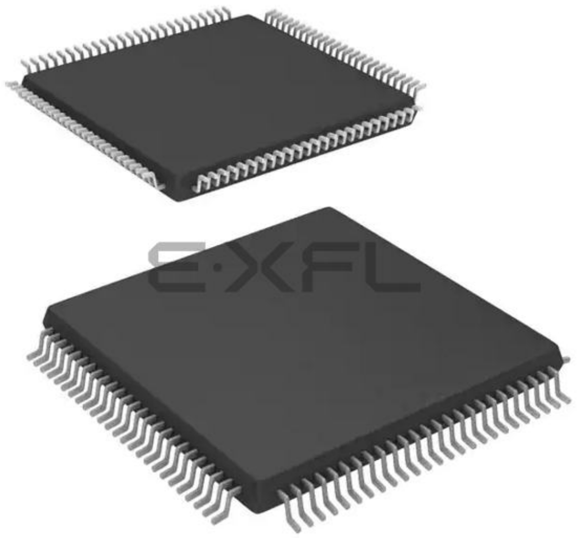
Microchip Technology - A3PN125-Z1VQ100I Datasheet



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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications,

Details	
Product Status	Obsolete
Number of LABs/CLBs	-
Number of Logic Elements/Cells	-
Total RAM Bits	36864
Number of I/O	71
Number of Gates	125000
Voltage - Supply	1.425V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	100-TQFP
Supplier Device Package	100-VQFP (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/a3pn125-z1vq100i

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Table 2-4 shows the current draw in Sleep mode for an A3P250 device with the following test conditions: VCCI = VMV; VCC = VJTAG = VPUMP = GND.

Table 2-4 **• A3P250 Current Draw in Sleep Mode**

Typical Conditions	**A3P250**	
	I_{CCI} (µA)	**I_{CCI} (µA) per Bank**
VCCI = 3.3 V	31.57	7.89
VCCI = 2.5 V	23.96	5.99
VCCI = 1.8 V	17.32	4.33
VCCI = 1.5 V	14.46	3.62
I_{CC} FPGA Core	0.0	0.0
Leakage Current per I/O	0.1	0.1
VPUMP	0.0	0.0

Note: The data in this table were taken under typical conditions and are based on characterization. The data is not guaranteed.

Table 2-5 shows the current draw in Sleep mode for an A3PE600 device with the following test conditions: VCCI = VMV; VCC = VJTAG = VPUMP = GND.

Table 2-5 **• A3PE600 Current Draw in Sleep Mode**

Typical Conditions	**A3PE600**	
	I_{CCI} (µA)	**I_{CCI} (µA) per Bank**
VCCI = 3.3 V	59.85	7.48
VCCI = 2.5 V	45.50	5.69
VCCI = 1.8 V	32.98	4.12
VCCI = 1.5 V	27.66	3.46
VCCI = 0 V or Floating	0.0	0.0
I_{CC} FPGA Core	0.0	0.0
Leakage Current per I/O	0.1	0.1
I_{PUMP}	0.0	0.0

Note: The data in this table were taken under typical conditions and are based on characterization. The data is not guaranteed.

ProASIC3/E and ProASIC3 nano devices were designed such that before device power-up, all I/Os are in tristate mode. The I/Os will remain tristated during power-up until the last voltage supply (VCC or VCCI) is powered to its functional level. After the last supply reaches the functional level, the outputs will exit the tristate mode and drive the logic at the input of the output buffer. The behavior of user I/Os is independent of the VCC and VCCI sequence or the state of other FPGA voltage supplies (VPUMP and VJTAG). During power-down, device I/Os become tristated once the first power supply (VCC or VCCI) drops below its brownout voltage level. The I/O behavior during power-down is also independent of voltage supply sequencing.

Figure 2-5 on page 27 shows a timing diagram for the FPGA core entering the activation and deactivation trip points for a typical application when the VCC power supply ramp rate is 100 µs (ramping from 0 V to 1.5 V). This is, in fact, the timing diagram for the FPGA entering and exiting Sleep mode, as it is dependent on powering down or powering up VCC. Depending on the ramp rate of the power supply and board-level configurations, the user can easily calculate how long it takes for the core to become active or inactive. For more information, refer to the "Power-Up/-Down Behavior of Low Power Flash Devices" section on page 307.

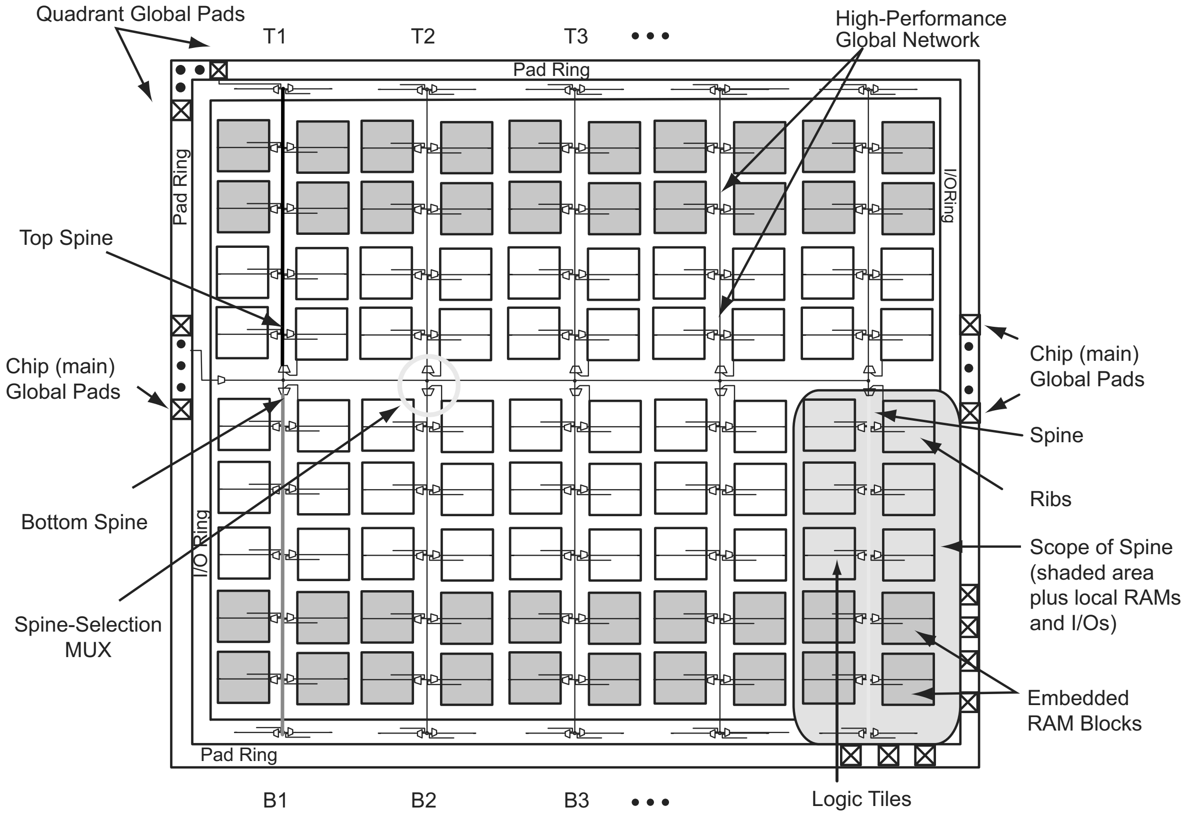
VersaNet Global Network Distribution

One of the architectural benefits of low power flash architecture is the set of powerful, low-delay VersaNet global networks that can access the VersaTiles, SRAM, and I/O tiles of the device. Each device offers a chip global network with six global lines (except for nano 10 k, 15 k, and 20 k gate devices) that are distributed from the center of the FPGA array. In addition, each device (except the 10 k through 30 k gate device) has four quadrant global networks, each consisting of three quadrant global net resources. These quadrant global networks can only drive a signal inside their own quadrant. Each VersaTile has access to nine global line resources—three quadrant and six chip-wide (main) global networks—and a total of 18 globals are available on the device (3 × 4 regional from each quadrant and 6 global).

Figure 3-1 shows an overview of the VersaNet global network and device architecture for devices 60 k and above. Figure 3-2 and Figure 3-3 on page 34 show simplified VersaNet global networks.

The VersaNet global networks are segmented and consist of spines, global ribs, and global multiplexers (MUXes), as shown in Figure 3-1. The global networks are driven from the global rib at the center of the die or quadrant global networks at the north or south side of the die. The global network uses the MUX trees to access the spine, and the spine uses the clock ribs to access the VersaTile. Access is available to the chip or quadrant global networks and the spines through the global MUXes. Access to the spine using the global MUXes is explained in the "Spine Architecture" section on page 41.

These VersaNet global networks offer fast, low-skew routing resources for high-fanout nets, including clock signals. In addition, these highly segmented global networks offer users the flexibility to create low-skew local clock networks using spines for up to 252 internal/external clocks or other high-fanout nets in low power flash devices. Optimal usage of these low-skew networks can result in significant improvement in design performance.



Note: Not applicable to 10 k through 30 k gate devices

***Figure 3-1* • Overview of VersaNet Global Network and Device Architecture**

Global Macro and Placement Selections

Low power flash devices provide the flexibility of choosing one of the three global input pad locations available to connect to a global / quadrant global network. For 60K gate devices and above, if the single-ended I/O standard is chosen, there is flexibility to choose one of the global input pads (the first, second, and fourth input). Once chosen, the other I/O locations are used as regular I/Os. If the differential I/O standard is chosen, the first and second inputs are considered as paired, and the third input is paired with a regular I/O. The user then has the choice of selecting one of the two sets to be used as the global input source. There is also the option to allow an internal clock signal to feed the global network. A multiplexer tree selects the appropriate global input for routing to the desired location. Note that the global I/O pads do not need to feed the global network; they can also be used as regular I/O pads.

Hardwired I/O Clock Source

Hardwired I/O refers to global input pins that are hardwired to the multiplexer tree, which directly accesses the global network. These global input pins have designated pin locations and are indicated with the I/O naming convention Gmn (m refers to any one of the positions where the global buffers is available, and n refers to any one of the three global input MUXes and the pin number of the associated global location, m). Choosing this option provides the benefit of directly connecting to the global buffers, which provides less delay. See Figure 3-11 for an example illustration of the connections, shown in red. If a CLKBUF macro is initiated, the clock input can be placed at one of nine dedicated global input pin locations: GmA0, GmA1, GmA2, GmB0, GmB1, GmB2, GmC0, GmC1, or GmC2. Note that the placement of the global will determine whether you are using chip global or quadrant global. For example, if the CLKBIF is placed in one of the GF pin locations, it will use the chip global network; if the CLKBIF is placed in one of the GA pin locations, it will use quadrant global network. This is shown in Figure 3-12 on page 49 and Figure 3-13 on page 49.

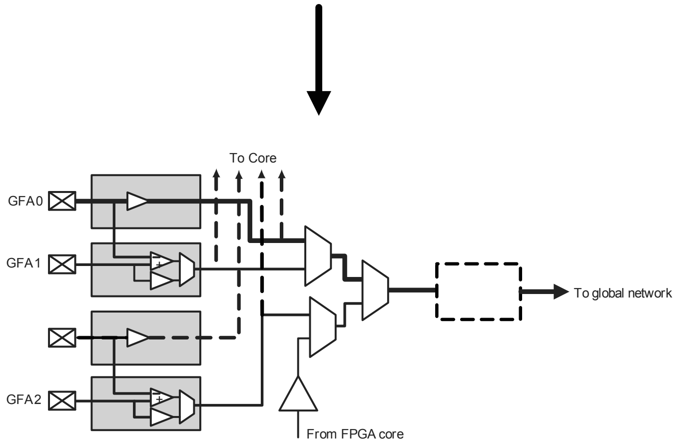


Figure 3-11 **• CLKBUF Macro**

During Layout, Designer will assign two of the signals to quadrant global locations.

Step 3 (optional)

You can also assign the QCLK1_c and QCLK2_c nets to quadrant regions using the following PDC commands:

```
assign_local_clock –net QCLK1_c  –type quadrant UL
assign_local_clock –net QCLK2_c  –type quadrant LL
```

Step 4

Import this PDC with the netlist and run Compile again. You will see the following in the Compile report:

```
The following nets have been assigned to a global resource:
Fanout  Type          Name
--------------------------
1536    INT_NET       Net   : EN_ALL_c
                      Driver: EN_ALL_pad_CLKINT
                      Source: AUTO PROMOTED
1536    SET/RESET_NET Net   : ACLR_c
                      Driver: ACLR_pad_CLKINT
                      Source: AUTO PROMOTED
256     CLK_NET       Net   : QCLK3_c
                      Driver: QCLK3_pad_CLKINT
                      Source: AUTO PROMOTED
256     CLK_NET       Net   : $1N14
                      Driver: $1I5/Core
                      Source: ESSENTIAL
256     CLK_NET       Net   : $1N12
                      Driver: $1I6/Core
                      Source: ESSENTIAL
256     CLK_NET       Net   : $1N10
                      Driver: $1I6/Core
                      Source: ESSENTIAL
The following nets have been assigned to a quadrant clock resource using PDC:
Fanout  Type          Name
--------------------------
256     CLK_NET       Net   : QCLK1_c
                      Driver: QCLK1_pad_CLKINT
                      Region: quadrant_UL
256     CLK_NET       Net   : QCLK2_c
                      Driver: QCLK2_pad_CLKINT
                      Region: quadrant_LL
```

Step 5

Run Layout.

Global Management in PLL Design

This section describes the legal global network connections to PLLs in the low power flash devices. For detailed information on using PLLs, refer to "Clock Conditioning Circuits in Low Power Flash Devices and Mixed Signal FPGAs" section on page 61. Microsemi recommends that you use the dedicated global pins to directly drive the reference clock input of the associated PLL for reduced propagation delays and clock distortion. However, low power flash devices offer the flexibility to connect other signals to reference clock inputs. Each PLL is associated with three global networks (Figure 3-5 on page 36). There are some limitations, such as when trying to use the global and PLL at the same time:

- If you use a PLL with only primary output, you can still use the remaining two free global networks.
- If you use three globals associated with a PLL location, you cannot use the PLL on that location.
- If the YB or YC output is used standalone, it will occupy one global, even though this signal does not go to the global network.

***Figure 4-34* • Cascade PLL Configuration**

Using internal feedback, we know from EQ 4-1 on page 86 that the maximum achievable output frequency from the primary output is

$$f_{GLA} = f_{CLKA} \times m / (n \times u) = 2\text{ MHz} \times 128 / (1 \times 1) = 256\text{ MHz}$$

EQ 4-5

Figure 4-35 shows the settings of the initial PLL. When configuring the initial PLL, specify the input to be either Hardwired I/O–Driven or External I/O–Driven. This generates a netlist with the initial PLL routed from an I/O. Do not specify the input to be Core Logic–Driven, as this prohibits the connection from the I/O pin to the input of the PLL.

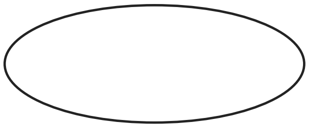


***Figure 4-35* • First-Stage PLL Showing Input of 2 MHz and Output of 256 MHz**

A second PLL can be connected serially to achieve the required frequency. EQ 4-1 on page 86 to EQ 4-3 on page 86 are extended as follows:

$$f_{GLA2} = f_{GLA} \times m_2 / (n_2 \times u_2) = f_{CLKA1} \times m_1 \times m_2 / (n_1 \times u_1 \times n_2 \times u_2) \text{ – Primary PLL Output Clock}$$

EQ 4-6

$$f_{GLB2} = f_{YB2} = f_{CLKA1} \times m_1 \times m_2 / (n_1 \times n_2 \times v_1 \times v_2) \text{ – Secondary 1 PLL Output Clock(s)}$$

EQ 4-7

$$f_{GLC2} = f_{YC2} = f_{CLKA1} \times m_1 \times m_2 / (n_1 \times n_2 \times w_1 \times w2) \text{ – Secondary 2 PLL Output Clock(s)}$$

EQ 4-8

In the example, the final output frequency (f_{output}) from the primary output of the second PLL will be as follows (EQ 4-9):

$$f_{output} = f_{GLA2} = f_{GLA} \times m_2 / (n_2 \times u_2) = 256\text{ MHz} \times 70 / (64 \times 1) = 280\text{ MHz}$$

EQ 4-9

Figure 4-36 on page 111 shows the settings of the second PLL. When configuring the second PLL (or any subsequent-stage PLLs), specify the input to be Core Logic–Driven. This generates a netlist with the second PLL routed internally from the core. Do not specify the input to be Hardwired I/O–Driven or External I/O–Driven, as these options prohibit the connection from the output of the first PLL to the input of the second PLL.

Figure 4-36 • **Second-Stage PLL Showing Input of 256 MHz from First Stage and Final Output of 280 MHz**

Figure 4-37 shows the simulation results, where the first PLL's output period is 3.9 ns (~256 MHz), and the stage 2 (final) output period is 3.56 ns (~280 MHz).

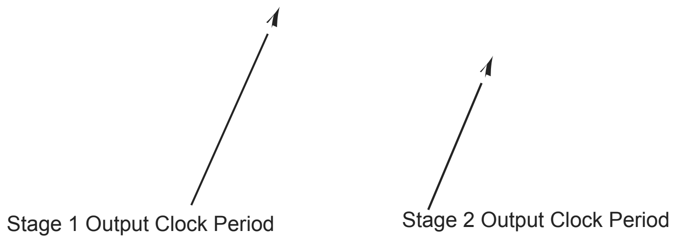


Figure 4-37 • **Model*Sim* Simulation Results**

Programming and Accessing FlashROM

The FlashROM content can only be programmed via JTAG, but it can be read back selectively through the JTAG programming interface, the UJTAG interface, or via direct FPGA core addressing. The pages of the FlashROM can be made secure to prevent read-back via JTAG. In that case, read-back on these secured pages is only possible by the FPGA core fabric or via UJTAG.

A 7-bit address from the FPGA core defines which of the eight pages (three MSBs) is being read, and which of the 16 bytes within the selected page (four LSBs) are being read. The FlashROM content can be read on a random basis; the access time is 10 ns for a device supporting commercial specifications. The FPGA core will be powered down during writing of the FlashROM content. FPGA power-down during FlashROM programming is managed on-chip, and FPGA core functionality is not available during programming of the FlashROM. Table 5-2 summarizes various FlashROM access scenarios.

***Table 5-2* • FlashROM Read/Write Capabilities by Access Mode**

Access Mode	FlashROM Read	FlashROM Write
JTAG	Yes	Yes
UJTAG	Yes	No
FPGA core	Yes	No

Figure 5-6 shows the accessing of the FlashROM using the UJTAG macro. This is similar to FPGA core access, where the 7-bit address defines which of the eight pages (three MSBs) is being read and which of the 16 bytes within the selected page (four LSBs) are being read. Refer to the "UJTAG Applications in Microsemi’s Low Power Flash Devices" section on page 297 for details on using the UJTAG macro to read the FlashROM.

Figure 5-7 on page 123 and Figure 5-8 on page 123 show the FlashROM access from the JTAG port. The FlashROM content can be read on a random basis. The three-bit address defines which page is being read or updated.

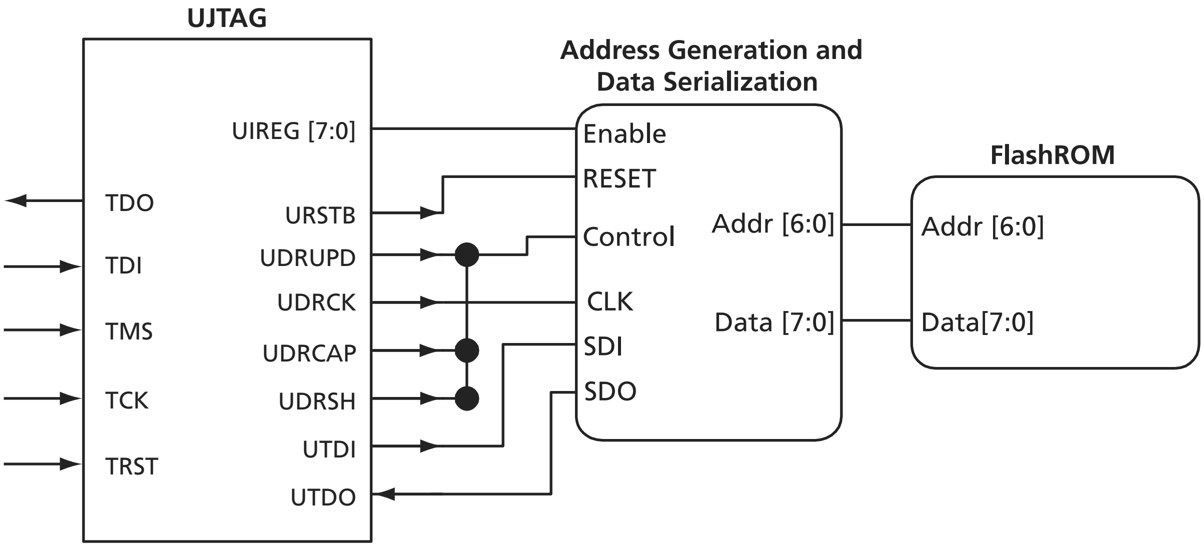
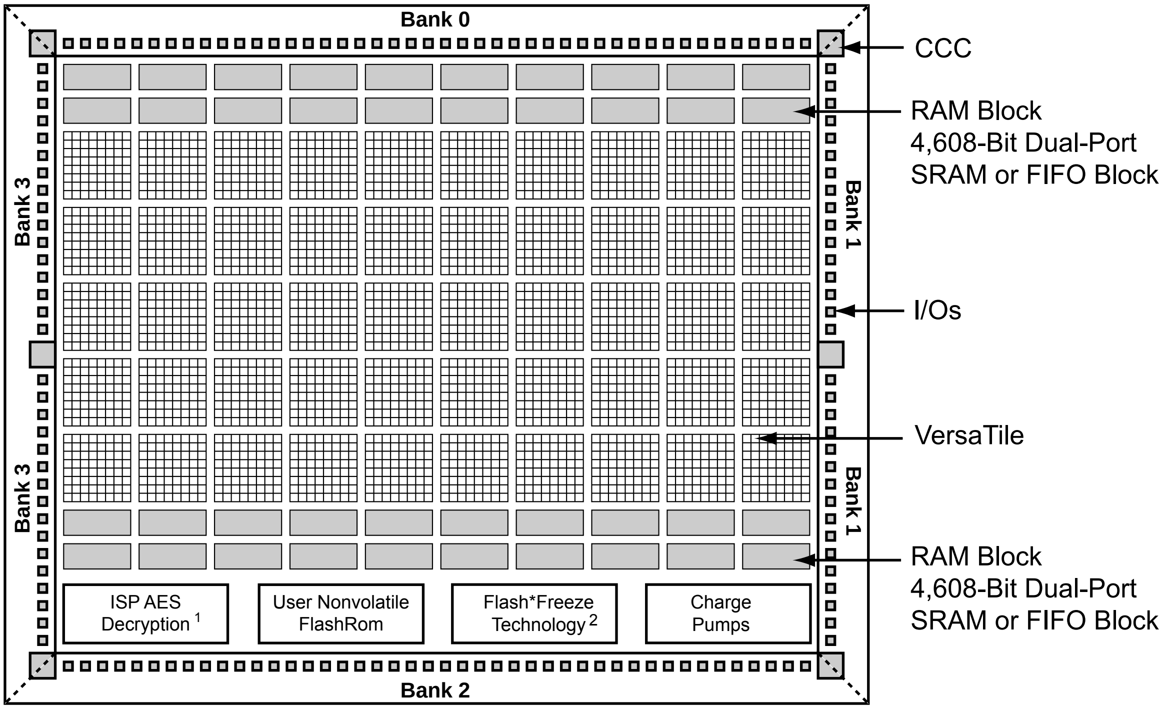


***Figure 5-6* • Block Diagram of Using UJTAG to Read FlashROM Contents**



Notes:

1. *AES decryption not supported in 30 k gate devices and smaller.*
2. *Flash*Freeze is supported in all IGLOO devices and the ProASIC3L devices.*

Figure 6-1 **• IGLOO and ProASIC3 Device Architecture Overview**

```
//
addr_counter counter_1 (.Clock(data_update), .Q(wr_addr), .Aset(rst_n),
  .Enable(enable));
addr_counter counter_2 (.Clock(test_clk), .Q(rd_addr), .Aset(rst_n),
  .Enable( test_active));

endmodule
```

Interface Block / UJTAG Wrapper

This example is a sample wrapper, which connects the interface block to the UJTAG and the memory blocks.

```
// WRAPPER
module top_init (TDI, TRSTB, TMS, TCK, TDO, test, test_clk, test_ out);

input TDI, TRSTB, TMS, TCK;
output TDO;
input test, test_clk;
output [3:0] test_out;

wire [7:0] IR;
wire reset, DR_shift, DR_cap, init_clk, DR_update, data_in, data_out;
wire clk_out, wen, ren;
wire [3:0] word_in, word_out;
wire [1:0] write_addr, read_addr;

UJTAG UJTAG_U1 (.UIREG0(IR[0]), .UIREG1(IR[1]), .UIREG2(IR[2]), .UIREG3(IR[3]),
  .UIREG4(IR[4]), .UIREG5(IR[5]), .UIREG6(IR[6]), .UIREG7(IR[7]), .URSTB(reset),
  .UDRSH(DR_shift), .UDRCAP(DR_cap), .UDRCK(init_clk), .UDRUPD(DR_update),
  .UT-DI(data_in), .TDI(TDI), .TMS(TMS), .TCK(TCK), .TRSTB(TRSTB), .TDO(TDO),
  .UT-DO(data_out));
mem_block RAM_block (.DO(word_out), .RCLOCK(clk_out), .WCLOCK(clk_out), .DI(word_in),
  .WRB(wen), .RDB(ren), .WAD-DR(write_addr), .RADDR(read_addr));
interface init_block (.IR(IR), .rst_n(reset), .data_shift(DR_shift), .clk_in(init_clk),
  .data_update(DR_update), .din_ser(data_in), .dout_ser(data_out), .test(test),
  .test_out(test_out), .test_clk(test_clk), .clk_out(clk_out), .wr_en(wen),
  .rd_en(ren), .write_word(word_in), .read_word(word_out), .rd_addr(read_addr),
  .wr_addr(write_addr));

endmodule
```

Address Counter

```
module addr_counter (Clock, Q, Aset, Enable);

input Clock;
output [1:0] Q;
input Aset;
input Enable;

reg [1:0] Qaux;

always @(posedge Clock or negedge Aset)
begin
  if (!Aset) Qaux <= 2'b11;
  else if (Enable) Qaux <= Qaux + 1;
end

assign Q = Qaux;

endmodule
```

Conclusion

Fusion, IGLOO, and ProASIC3 devices provide users with extremely flexible SRAM blocks for most design needs, with the ability to choose between an easy-to-use dual-port memory or a wide-word two-port memory. Used with the built-in FIFO controllers, these memory blocks also serve as highly efficient FIFOs that do not consume user gates when implemented. The SmartGen core generator provides a fast and easy way to configure these memory elements for use in designs.

List of Changes

The following table lists critical changes that were made in each revision of the chapter.

Date	Changes	Page
August 2012	The note connected with Figure 6-3 • Supported Basic RAM Macros, regarding RAM4K9, was revised to explain that it applies only to part numbers of certain revisions and earlier (SAR 29574).	136
July 2010	This chapter is no longer published separately with its own part number and version but is now part of several FPGA fabric user's guides.	N/A
v1.5 (December 2008)	IGLOO nano and ProASIC3 nano devices were added to Table 6-1 • Flash-Based FPGAs.	134
	IGLOO nano and ProASIC3 nano devices were added to Figure 6-8 • Interfacing TAP Ports and SRAM Blocks.	148
v1.4 (October 2008)	The "SRAM/FIFO Support in Flash-Based Devices" section was revised to include new families and make the information more concise.	134
	The "SRAM and FIFO Architecture" section was modified to remove "IGLOO and ProASIC3E" from the description of what the memory block includes, as this statement applies to all memory blocks.	135
	Wording in the "Clocking" section was revised to change "IGLOO and ProASIC3 devices support inversion" to "Low power flash devices support inversion." The reference to IGLOO and ProASIC3 development tools in the last paragraph of the section was changed to refer to development tools in general.	141
	The "ESTOP and FSTOP Usage" section was updated to refer to FIFO counters in devices in general rather than only IGLOO and ProASIC3E devices.	144
v1.3 (August 2008)	The note was removed from Figure 6-7 • RAM Block with Embedded FIFO Controller and placed in the WCLK and RCLK description.	142
	The "WCLK and RCLK" description was revised.	143
v1.2 (June 2008)	The following changes were made to the family descriptions in Table 6-1 • Flash-Based FPGAs: • ProASIC3L was updated to include 1.5 V. • The number of PLLs for ProASIC3E was changed from five to six.	134
v1.1 (March 2008)	The "Introduction" section was updated to include the IGLOO PLUS family.	131
	The "Device Architecture" section was updated to state that 15 k gate devices do not support SRAM and FIFO.	131
	The first note in Figure 6-1 • IGLOO and ProASIC3 Device Architecture Overview was updated to include mention of 15 k gate devices, and IGLOO PLUS was added to the second note.	133

Table 7-13 • **Comparison Table for 5 V–Compliant Receiver Solutions**

Solution	Board Components	Speed	Current Limitations
1	Two resistors	Low to High[1]	Limited by transmitter's drive strength
2	Resistor and Zener 3.3 V	Medium	Limited by transmitter's drive strength
3	Bus switch	High	N/A

Notes:

1. *Speed and current consumption increase as the board resistance values decrease.*
2. *Resistor values ensure I/O diode long-term reliability.*
3. *At 70°C, customers could still use 420 Ω on every I/O.*
4. *At 85°C, a 5 V solution on every other I/O is permitted, since the resistance is lower (150 Ω) and the current is higher. Also, the designer can still use 420 Ω and use the solution on every I/O.*
5. *At 100°C, the 5 V solution on every I/O is permitted, since 420 Ω are used to limit the current to 5.9 mA.*

5 V Output Tolerance

nano Standard I/Os must be set to 3.3 V LVTTL or 3.3 V LVCMOS mode to reliably drive 5 V TTL receivers. It is also critical that there be NO external I/O pull-up resistor to 5 V, since this resistor would pull the I/O pad voltage beyond the 3.6 V absolute maximum value and consequently cause damage to the I/O.

When set to 3.3 V LVTTL or 3.3 V LVCMOS mode, the I/Os can directly drive signals into 5 V TTL receivers. In fact, V_{OL} = 0.4 V and V_{OH} = 2.4 V in both 3.3 V LVTTL and 3.3 V LVCMOS modes exceeds the V_{IL} = 0.8 V and V_{IH} = 2 V level requirements of 5 V TTL receivers. Therefore, level 1 and level 0 will be recognized correctly by 5 V TTL receivers.

Schmitt Trigger

A Schmitt trigger is a buffer used to convert a slow or noisy input signal into a clean one before passing it to the FPGA. Using Schmitt trigger buffers guarantees a fast, noise-free input signal to the FPGA.

nano devices have Schmitt triggers built into their I/O circuitry. Schmitt Trigger is available on all I/O configurations.

This feature can be implemented by using a Physical Design Constraints (PDC) command (Table 7-5 on page 163) or by selecting a check box in the I/O Attribute Editor in Designer. The check box is cleared by default.

I/O Register Combining

Every I/O has several embedded registers in the I/O tile that are close to the I/O pads. Rather than using the internal register from the core, the user has the option of using these registers for faster clock-to-out timing, and external hold and setup. When combining these registers at the I/O buffer, some architectural rules must be met. Provided these rules are met, the user can enable register combining globally during Compile (as shown in the "Compiling the Design" section in the "I/O Software Control in Low Power Flash Devices" section on page 185.

This feature is supported by all I/O standards.

Rules for Registered I/O Function:

1. The fanout between an I/O pin (D, Y, or E) and a register must be equal to one for combining to be considered on that pin.
2. All registers (Input, Output, and Output Enable) connected to an I/O must share the same clear or preset function:
   - If one of the registers has a CLR pin, all the other registers that are candidates for combining in the I/O must have a CLR pin.

User I/O Naming Convention

Due to the comprehensive and flexible nature of nano Standard I/Os, a naming scheme is used to show the details of each I/O (Figure 7-8). The name identifies to which I/O bank it belongs.

I/O Nomenclature = FF/Gmn/IOuxwBy

Gmn is only used for I/Os that also have CCC access—i.e., global pins.

FF = Indicates the I/O dedicated for the Flash*Freeze mode activation pin

G = Global

m = Global pin location associated with each CCC on the device: A (northwest corner), B (northeast corner), C (east middle), D (southeast corner), E (southwest corner), and F (west middle)

n = Global input MUX and pin number of the associated Global location m—either A0, A1, A2, B0, B1, B2, C0, C1, or C2. Refer to the "Global Resources in Low Power Flash Devices" section on page 31 for information about the three input pins per clock source MUX at CCC location m.

u = I/O pair number in the bank, starting at 00 from the northwest I/O bank and proceeding in a clockwise direction

x = R (Regular—single-ended) for the I/Os that support single-ended standards.

w = S (Single-Ended)

B = Bank

y = Bank number (0–3). The Bank number starts at 0 from the northwest I/O bank and proceeds in a clockwise direction.

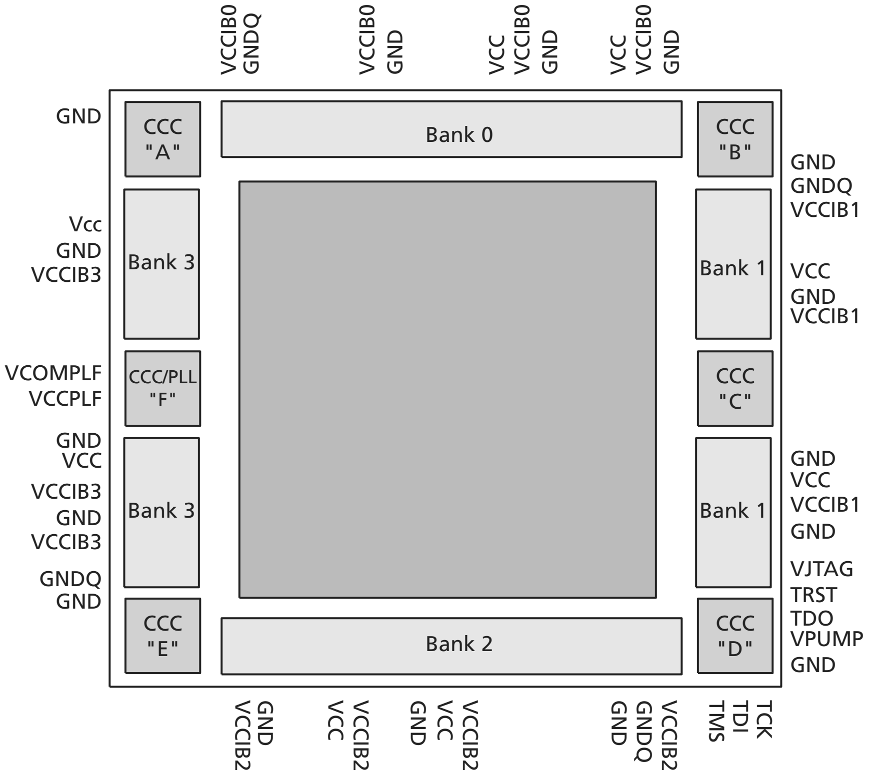


Figure 7-8 • **I/O Naming Conventions for nano Devices – Top View**

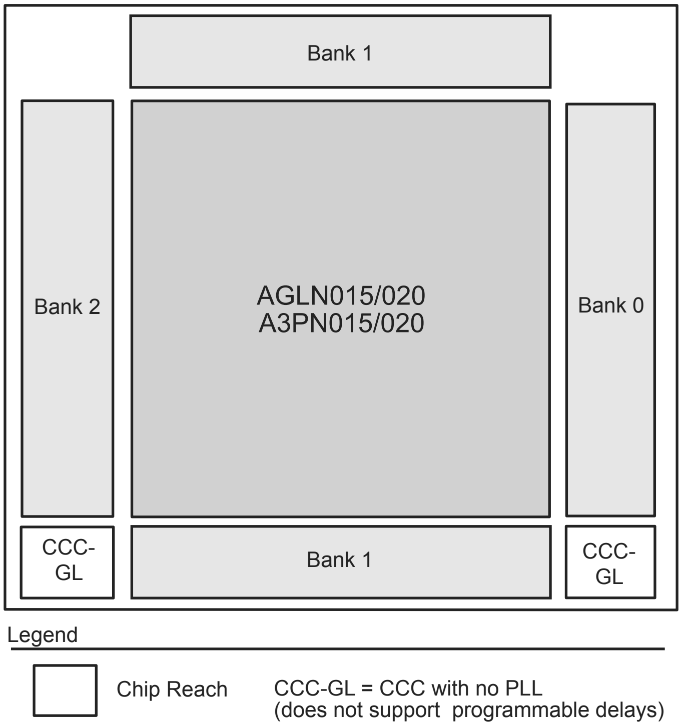


Figure 7-10 • **I/O Bank Architecture of AGLN015/020 and A3PN015/020 Devices**

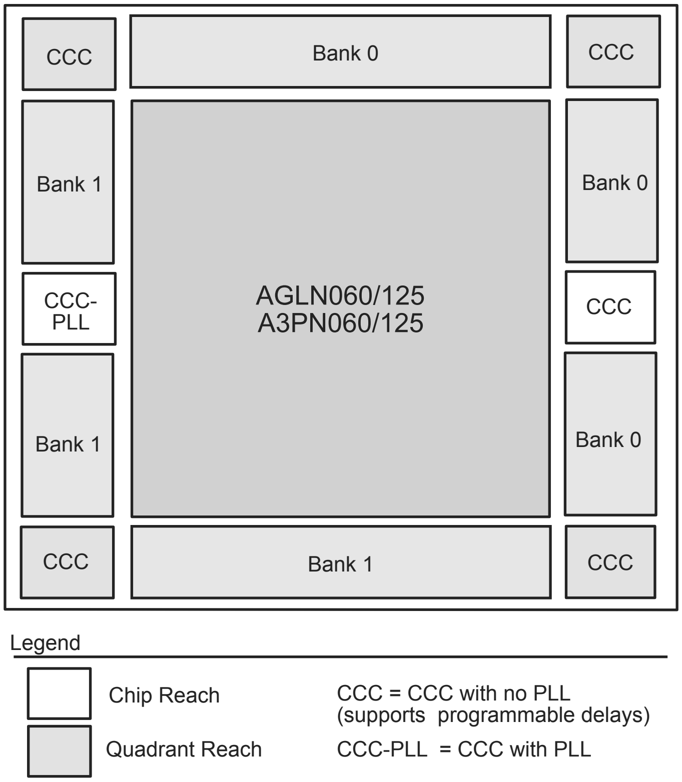


Figure 7-11 • **I/O Bank Architecture of AGLN060/125 and A3PN060/125 Devices**

If the assignment is not successful, an error message appears in the Output window.

To undo the I/O bank assignments, choose **Undo** from the **Edit** menu. Undo removes the I/O technologies assigned by the IOBA. It does not remove the I/O technologies previously assigned.

To redo the changes undone by the Undo command, choose **Redo** from the **Edit** menu.

To clear I/O bank assignments made before using the Undo command, manually unassign or reassign I/O technologies to banks. To do so, choose **I/O Bank Settings** from the **Edit** menu to display the I/O Bank Settings dialog box.

Conclusion

Fusion, IGLOO, and ProASIC3 support for multiple I/O standards minimizes board-level components and makes possible a wide variety of applications. The Microsemi Designer software, integrated with Libero SoC, presents a clear visual display of I/O assignments, allowing users to verify I/O and board-level design requirements before programming the device. The device I/O features and functionalities ensure board designers can produce low-cost and low power FPGA applications fulfilling the complexities of contemporary design needs.

Related Documents

User's Guides

Libero SoC User's Guide

http://www.microsemi.com/soc/documents/libero_ug.pdf

IGLOO, ProASIC3, SmartFusion, and Fusion Macro Library Guide

http://www.microsemi.com/soc/documents/pa3_libguide_ug.pdf

SmartGen Core Reference Guide

http://www.microsemi.com/soc/documents/genguide_ug.pdf

DDR Support in Flash-Based Devices

The flash FPGAs listed in Table 9-1 support the DDR feature and the functions described in this document.

***Table 9-1* • Flash-Based FPGAs**

Series	Family*	Description
IGLOO	IGLOO	Ultra-low power 1.2 V to 1.5 V FPGAs with Flash*Freeze technology
	IGLOOe	Higher density IGLOO FPGAs with six PLLs and additional I/O standards
	IGLOO nano	The industry's lowest-power, smallest-size solution
ProASIC3	ProASIC3	Low power, high-performance 1.5 V FPGAs
	ProASIC3E	Higher density ProASIC3 FPGAs with six PLLs and additional I/O standards
	ProASIC3 nano	Lowest-cost solution with enhanced I/O capabilities
	ProASIC3L	ProASIC3 FPGAs supporting 1.2 V to 1.5 V with Flash*Freeze technology
	RT ProASIC3	Radiation-tolerant RT3PE600L and RT3PE3000L
	Military ProASIC3/EL	Military temperature A3PE600L, A3P1000, and A3PE3000L
	Automotive ProASIC3	ProASIC3 FPGAs qualified for automotive applications
Fusion	Fusion	Mixed signal FPGA integrating ProASIC3 FPGA fabric, programmable analog block, support for ARM® Cortex™-M1 soft processors, and flash memory into a monolithic device

*Note: *The device names link to the appropriate datasheet, including product brief, DC and switching characteristics, and packaging information.*

IGLOO Terminology

In documentation, the terms IGLOO series and IGLOO devices refer to all of the IGLOO devices as listed in Table 9-1. Where the information applies to only one product line or limited devices, these exclusions will be explicitly stated.

ProASIC3 Terminology

In documentation, the terms ProASIC3 series and ProASIC3 devices refer to all of the ProASIC3 devices as listed in Table 9-1. Where the information applies to only one product line or limited devices, these exclusions will be explicitly stated.

To further understand the differences between the IGLOO and ProASIC3 devices, refer to the *Industry's Lowest Power FPGAs Portfolio*.

I/O Cell Architecture

Low power flash devices support DDR in the I/O cells in four different modes: Input, Output, Tristate, and Bidirectional pins. For each mode, different I/O standards are supported, with most I/O standards having special sub-options. For the ProASIC3 nano and IGLOO nano devices, DDR is supported only in the 60 k, 125 k, and 250 k logic densities. Refer to Table 9-2 for a sample of the available I/O options. Additional I/O options can be found in the relevant family datasheet.

Table 9-2 **• DDR I/O Options**

DDR Register Type	I/O Type	I/O Standard	Sub-Options	Comments
Receive Register	Input	Normal	None	3.3 V TTL (default)
		LVCMOS	Voltage	1.5 V, 1.8 V, 2.5 V, 5 V (1.5 V default)
			Pull-Up	None (default)
		PCI/PCI-X	None	
		GTL/GTL+	Voltage	2.5 V, 3.3 V (3.3 V default)
		HSTL	Class	I / II (I default)
		SSTL2/SSTL3	Class	I / II (I default)
		LVPECL	None	
		LVDS	None	
Transmit Register	Output	Normal	None	3.3 V TTL (default)
		LVTTL	Output Drive	2, 4, 6, 8, 12, 16, 24, 36 mA (8 mA default)
			Slew Rate	Low/high (high default)
		LVCMOS	Voltage	1.5 V, 1.8 V, 2.5 V, 5 V (1.5 V default)
		PCI/PCI-X	None	
		GTL/GTL+	Voltage	1.8 V, 2.5 V, 3.3 V (3.3 V default)
		HSTL	Class	I / II (I default)
		SSTL2/SSTL3	Class	I / II (I default)
		LVPECL*	None	
		LVDS*	None	

*Note: *IGLOO nano and ProASIC3 nano devices do not support differential inputs.*

Figure 11-15 • **Programming Fusion Security Settings Only**

2. Choose the desired security level setting and enter the key(s).
   - The **High** security level employs FlashLock Pass Key with AES Key protection.
   - The **Medium** security level employs FlashLock Pass Key protection only.

Figure 11-16 • **High Security Level to Implement FlashLock Pass Key and AES Key Protection** errors, but this list is intended to show where problems can occur. FlashPro4/3/3X allows TCK to be lowered from 6 MHz down to 1 MHz to allow you to address some signal integrity problems that may occur with impedance mismatching at higher frequencies. Customers are expected to troubleshoot board-level signal integrity issues by measuring voltages and taking scope plots.

Scan Chain Failure

Normally, the FlashPro4/3/3X Scan Chain command expects to see 0x1 on the TDO pin. If the command reports reading 0x0 or 0x3, it is seeing the TDO pin stuck at 0 or 1. The only time the TDO pin comes out of tristate is when the JTAG TAP state machine is in the Shift-IR or Shift-DR state. If noise or reflections on the TCK or TMS lines have disrupted the correct state transitions, the device's TAP state controller might not be in one of these two states when the programmer tries to read the device. When this happens, the output is floating when it is read and does not match the expected data value. This can also be caused by a broken TDO net. Only a small amount of data is read from the device during the Scan Chain command, so marginal problems may not always show up during this command. Occasionally a faulty programmer can cause intermittent scan chain failures.

Exit 11

This error occurs during the verify stage of programming a device. After programming the design into the device, the device is verified to ensure it is programmed correctly. The verification is done by shifting the programming data into the device. An internal comparison is performed within the device to verify that all switches are programmed correctly. Noise induced by poor signal integrity can disrupt the writes and reads or the verification process and produce a verification error. While technically a verification error, the root cause is often related to signal integrity.

Refer to the *FlashPro User's Guide* for other error messages and solutions. For the most up-to-date known issues and solutions, refer to http://www.microsemi.com/soc/support.

Conclusion

IGLOO, ProASIC3, SmartFusion, and Fusion devices offer a low-cost, single-chip solution that is live at power-up through nonvolatile flash technology. The FlashLock Pass Key and 128-bit AES Key security features enable secure ISP in an untrusted environment. On-chip FlashROM enables a host of new applications, including device serialization, subscription-based applications, and IP addressing. Additionally, as the FlashROM is nonvolatile, all of these services can be provided without battery backup.

Related Documents

User's Guides

FlashPro User's Guide

http://www.microsemi.com/soc/documents/flashpro_ug.pdf

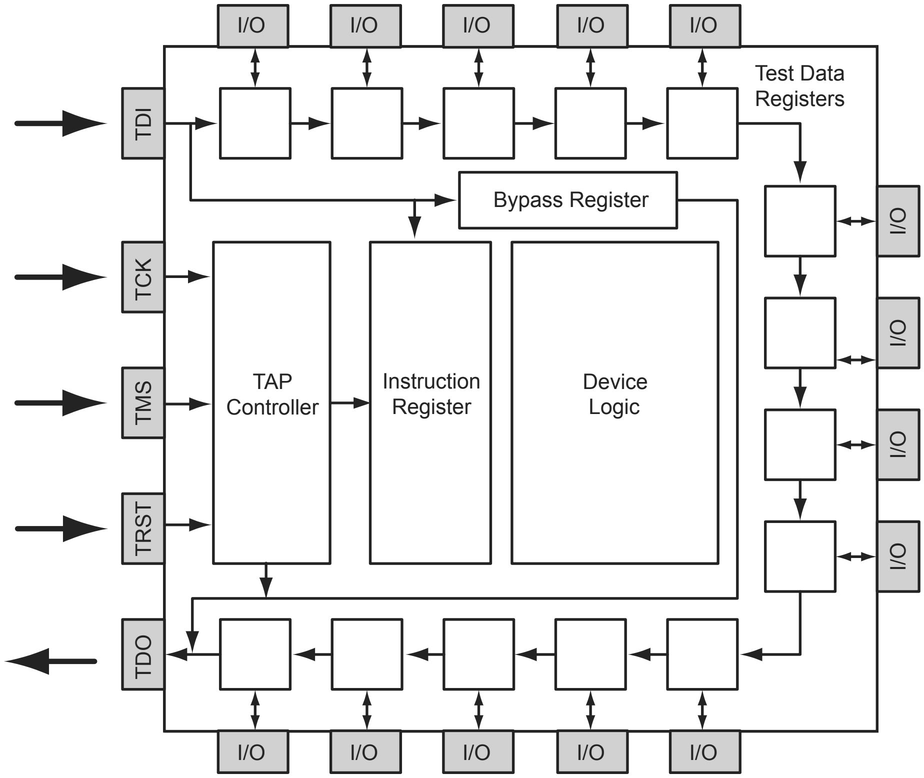


Figure 15-2 • **Boundary Scan Chain**

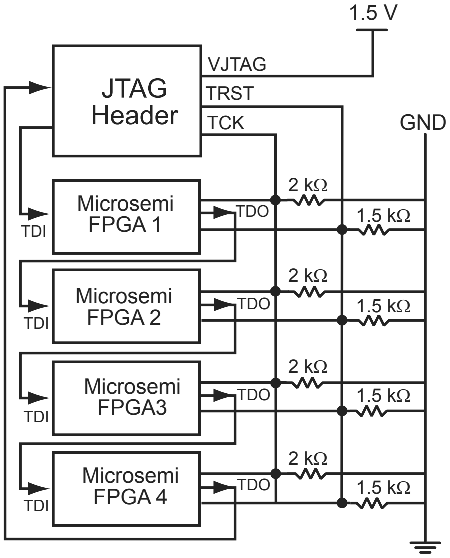
Board-Level Recommendations

Table 15-3 gives pull-down recommendations for the TRST and TCK pins.

Table 15-3 • **TRST and TCK Pull-Down Recommendations**

VJTAG	**Tie-Off Resistance***
VJTAG at 3.3 V	200 Ω to 1 kΩ
VJTAG at 2.5 V	200 Ω to 1 kΩ
VJTAG at 1.8 V	500 Ω to 1 kΩ
VJTAG at 1.5 V	500 Ω to 1 kΩ
VJTAG at 1.2 V	TBD

Note: Equivalent parallel resistance if more than one device is on JTAG chain (Figure 15-3)



Note: TCK is correctly wired with an equivalent tie-off resistance of 500 Ω, which satisfies the table for VJTAG of 1.5 V. The resistor values for TRST are not appropriate in this case, as the tie-off resistance of 375 Ω is below the recommended minimum for VJTAG = 1.5 V, but would be appropriate for a VJTAG setting of 2.5 V or 3.3 V.

***Figure 15-3* • Parallel Resistance on JTAG Chain of Devices**

Advanced Boundary Scan Register Settings

You will not be able to control the order in which I/Os are released from boundary scan control. Testing has produced cases where, depending on I/O placement and FPGA routing, a 5 ns glitch has been seen on exiting programming mode. The following setting is recommended to prevent such I/O glitches:

1. In the FlashPro software, configure the advanced BSR settings for **Specify I/O Settings During Programming**.
2. Set the input BSR cell to **Low** for the input I/O.